NMOS enhancement transister (duivor) Load 12 => load bannistus, NMOS Inverter 2.8

gate of T2 is Vp, so gsT2 is maximum So To is always ON. 1) When Vin = low Small leakage Ti So T, is 86 However, To is ON, brings To just to Conduction. So Ye drop Vp Vp Vont = Vp - Vte (1) 18 pld T2 = 5-1 = 4 V Vte S Vont De Whon Vin = Vp = 5 However, source terminal of T2 is not fixed (not grounded). So there exists significant body effect.  $V_{te} = V_{te0} + V \sqrt{V_{sb}} - - - (ii)$ putting the value of the in equin (i) Vout = Vp - Vteo - VVsb .... (iii)  $V_p = 3V$ ,  $V_{teo} = 1V$ ,  $V_s = V_{out}$ ,  $V_b = 0V$ and V = 0.5V

So 
$$V_{out} = 5 - 1 - 0.5 \sqrt{V_{out} - 0}$$
 $\Rightarrow 0.5 V_{out}^{V_2} = 4 - V_{out}$ 
 $\Rightarrow V_{out}^{V_2} = 8 - 2 V_{out}$ 

Squaring both sides,

 $V_{out} = 64 + 4 V_{out} - 32 V_{out}$ 
 $\Rightarrow 4 V_{out}^{\infty} - 33 V_{out} + 64 = 0$ 
 $\therefore V_{out} = \frac{+33 \pm \sqrt{33} - 4 \times 4 \times 64}{2 \times 4}$ 
 $= \frac{+33 \pm \sqrt{65}}{8} = +33 \pm 8.06$ 
 $= 5.13 \text{ or } 3.12 V$ 

Since  $V_{out} = 3.12 V$ 

This is the high output voltage due to dody effect.

So the high logic value of this cht is

 $V(1) = 3.12 V$  instead of  $5 V$ 
 $V(0) = 0 V$ 

Inverter Ratio Calculation For this Calculation, we have to select the case when  $V_{gs} = 3.12 V$   $V_{ds} = 0.3$   $V_{ds} = 0.3$ both Transistors Conduct. : Vds, < Vgs, - Vt : T, is in Resistive region  $I_{ds_1} = 30 \times \frac{\omega_1}{L_1} \times \left[ (3.12 - 1) \cdot 0.3 - \frac{0.3^{\circ}}{2} \right]$  $= 17.73 \left( \frac{\omega_l}{L_l} \right) \quad uA$ 

 $= 30 \times \frac{\omega_2}{L_2} \times \frac{1}{2} \times (4.7 - 1)^2$   $= 205.4 \times \frac{\omega_2}{L_2}$ 

Putting 
$$Ids_{1} = Ids_{2}$$
 $17.73 \frac{W_{1}}{L_{1}} = 205.4 \frac{W_{2}}{L_{2}}$ 
 $\Rightarrow K = \left(\frac{W_{1}}{L_{1}}\right)\left(\frac{W_{2}}{L_{2}}\right) = \frac{205.4}{17.73} = 11.6$ 

K ≈ 12

which is high for this inverter